Abstracts

Switches with capacitor cancelled parasitic inductance of FET

K. Nakahara, K. Miyaguchi, M. Hieda, H. Kurusu, Y. Iyama and T. Takagi. "Switches with capacitor cancelled parasitic inductance of FET." 2001 MTT-S International Microwave Symposium Digest 01.1 (2001 Vol. I [MWSYM]): 249-252 vol.1.

GaAs SPDT FET switches have been developed with capacitor cancelled parasitic inductance of FET. The switches employed series-shunt configuration. The switches have been shown to have significantly higher isolation and higher frequency operation compared to conventional switch. Isolation of 28.9 dB at 18 GHz and 30 GHz has been achieved.

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